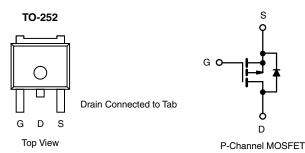


www.vishay.com

Vishay Siliconix

Automotive P-Channel 80 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	- 80			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.025			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.031			
I _D (A)	- 50			
Configuration	Single			



FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^d
- 100 % R_a and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P08-25L-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 80	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C ^a	L	- 50		
	T _C = 125 °C	l _D	- 28		
Continuous Source Current (Diode Conduction)a		I _S	- 50	Α	
Pulsed Drain Current ^b		I _{DM}	- 120		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 45		
Single Pulse Avalanche Energy	L=0.1 IIII	E _{AS}	100	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	P_{D}	136	W	
	T _C = 125 °C		45	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 80	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = - 250 μA	- 1.5	- 2.0	- 2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = - 80 V	1	-	- 1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -80 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	- 50	μΑ
		V _{GS} = 0 V	V _{DS} = - 80 V, T _J = 175 °C	-	-	- 250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≤ - 5 V	- 50	-	-	Α
		V _{GS} = - 10 V	I _D = - 12.5 A	-	0.020	0.025	
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V	I _D = - 12.5 A, T _J = 125 °C	-	-	0.044	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 12.5 A, T _J = 175 °C	-	-	0.055	Ω
		V _{GS} = - 4.5 V	I _D = - 10.5 A	-	0.025	0.031]
Forward Transconductanceb	9 _{fs}	V _{DS} = -	- 15 V, I _D = - 12.5 A	-	38	-	S
Dynamic ^b		•					
Input Capacitance	C _{iss}		V _{GS} = 0 V V _{DS} = - 25 V, f = 1 MHz	-	4279	5350	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	356	445	
Reverse Transfer Capacitance	C _{rss}			-	239	300	
Total Gate Charge ^c	Qg			-	91	137	
Gate-Source Charge ^c	Q_{gs}	$V_{GS} = -10 \text{ V}$	$V_{DS} = -40 \text{ V}, I_{D} = -12.5 \text{ A}$	-	8.2	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	24	-	
Gate Resistance	Rg	f = 1 MHz		1.60	3.26	5.00	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	10	15	
Rise Time ^c	t _r	$V_{DD} = \text{- 40 V}, R_L = 3.2 \Omega$ $I_D \cong \text{- 12.5 A}, V_{GEN} = \text{- 10 V}, R_g = 1 \Omega$		-	11	17	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	71	107	
Fall Time ^c	t _f			-	16	24	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	- 120	Α
Forward Voltage	V _{SD}	I _F = - 10.5 A, V _{GS} = 0 V		-	- 0.82	- 1.5	V

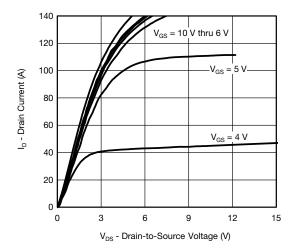
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

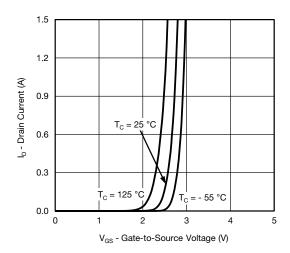
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



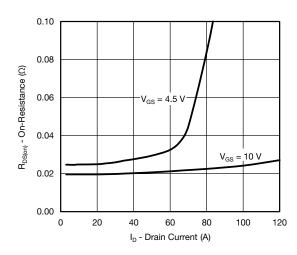
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



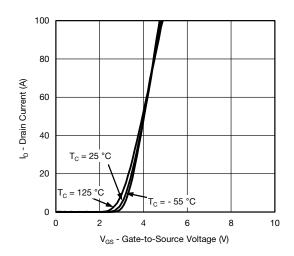
Output Characteristics



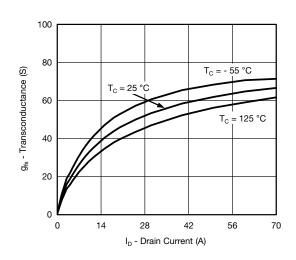
Transfer Characteristics



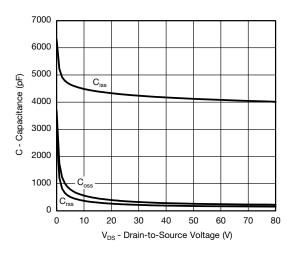
On-Resistance vs. Drain Current



Transfer Characteristics



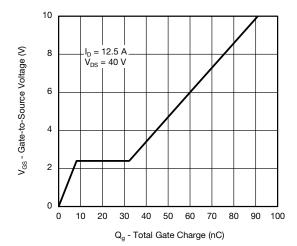
Transconductance



Capacitance

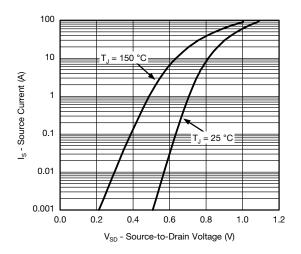


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

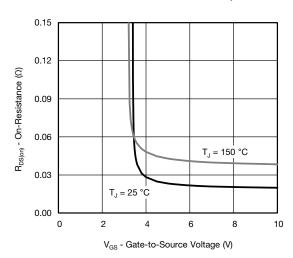


2.5 $I_D = 12.5 \text{ A}$ R_{DS(on)} - On-Resistance (Normalized) 2.1 $V_{GS} = 10$ 1.7 $V_{GS} = 4.5 \text{ V}$ 1.3 0.9 0.5 - 25 50 50 75 100 125 T_J - Junction Temperature (°C)

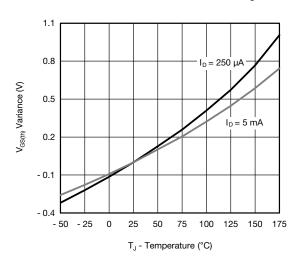
Gate Charge



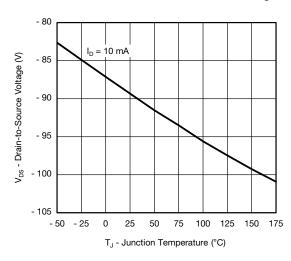
On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

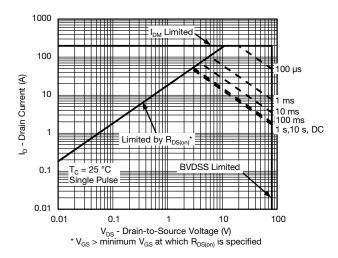


Threshold Voltage

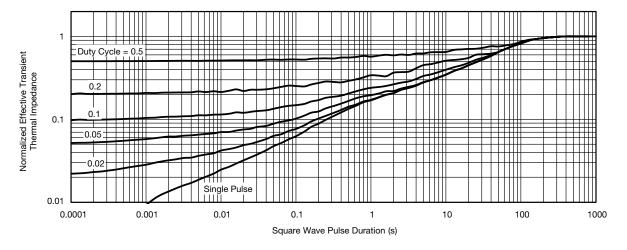
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



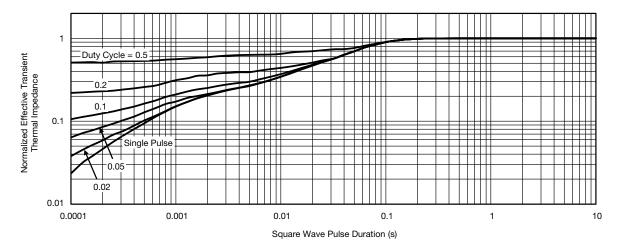
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

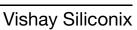


Normalized Thermal Transient Impedance, Junction-to-Case

Note

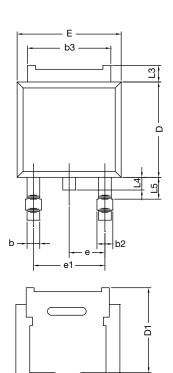
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

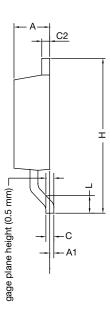
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72217.





TO-252AA Case Outline





	MILLIN	METERS	INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
Α	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
Е	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28	BSC	0.090	BSC
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T13-0592-Rev. A, 02-Sep-13				

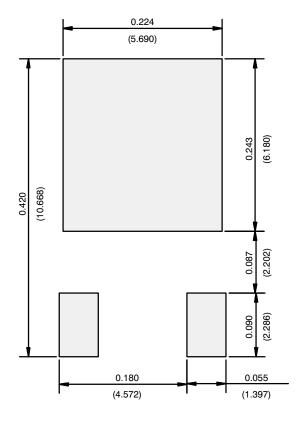
DWG: 6019

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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